National Semiconductor is now part of

Texas Instruments.

Search <u>http://www.ti.com/</u> for the latest technical

information and details on our current products and services.



DS25MB200

Dual 2.5 Gbps 2:1/1:2 CML Mux/Buffer with Transmit Pre-Emphasis and Receive Equalization

General Description

The DS25MB200 is a dual signal conditioning 2:1 multiplexer and 1:2 fan-out buffer designed for use in backplane redundancy applications. Signal conditioning features include input equalization and programmable output pre-emphasis that enable data communication in FR4 backplanes up to 2.5 Gbps. Each input stage has a fixed equalizer to reduce ISI distortion from board traces. All output drivers have 4 selectable steps of pre-emphasis to compensate for transmission losses from long FR4 backplanes and reduce deterministic jitter. The pre-emphasis levels can be independently controlled for the lineside and switch-side drivers. The internal loopback paths from switch-side input to switch-side output enable at-speed system testing. All receiver inputs are internally terminated with 100 Ω differential terminating resistors. All drivers are internally terminated with 50 Ω to $V_{\rm CC}$.

Features

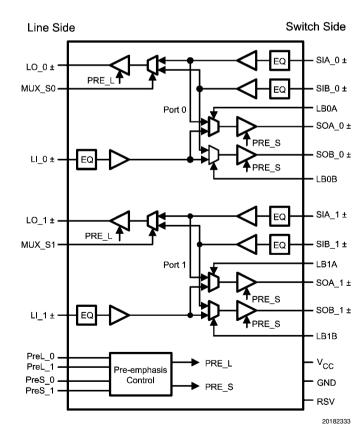
- 0.6–2.5 Gbps low jitter operation
- Fixed input equalization
- Programmable output pre-emphasis
- Independent switch and line side pre-emphasis controls

February 24, 2009

- Programmable switch-side loopback modes
- On-chip terminations
- HBM ESD rating 6 kV on all pins
- +3.3V supply
- Lead-less LLP-48 package (7mm x 7mm x 0.8mm, 0.5mm pitch)
- —40°C to +85°C operating temperature range

Applications

- Backplane or cable driver
- Redundancy and signal conditioning applications

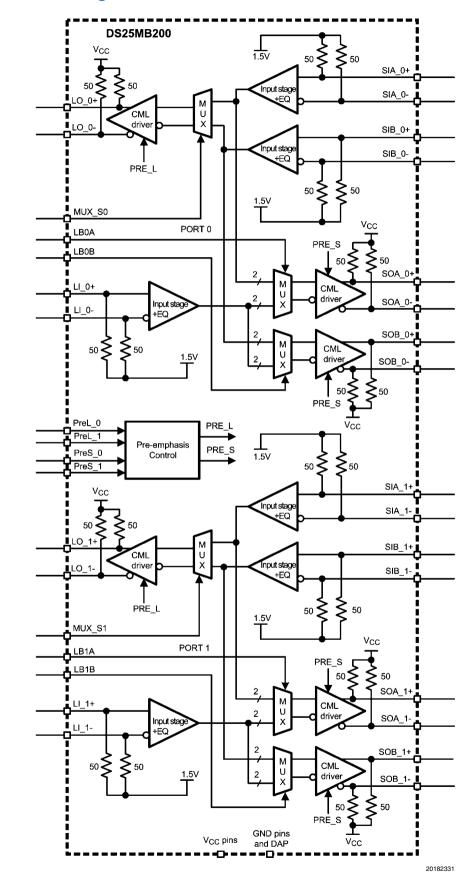


Functional Block Diagram

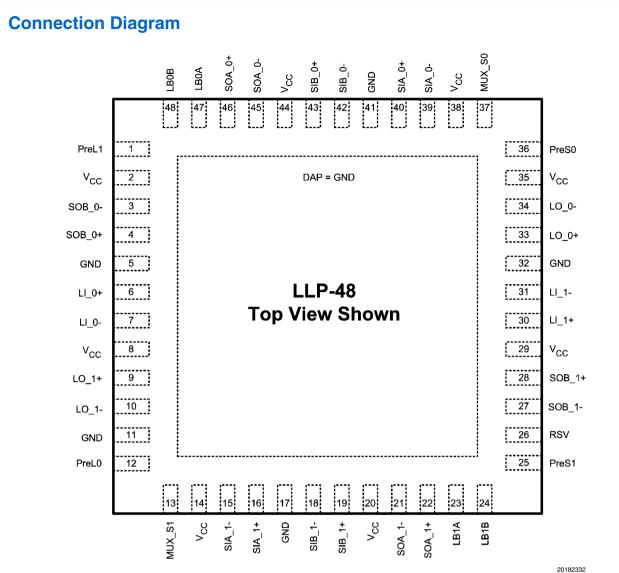
Note: All CML inputs and outputs must be AC coupled for optimal performance.

DS25MB200

Simplified Block Diagram



www.national.com



Order Number DS25MB200TSQ See NS Package Number NSQAV48 **DS25MB200**

Pin Descriptions

Pin Name	Pin Number	I/O	Description
LINE SIDE H	IGH SPEED D	IFFER	ENTIAL IO's
LI_0+	6	I	Inverting and non-inverting differential inputs of port_0 at the line side. LI_0+ and LI_0- have an
LI_0-	7		internal 50 Ω connected to an internal reference voltage. See <i>Figure 6</i> .
LO_0+	33	0	Inverting and non-inverting differential outputs of port_0 at the line side. LO_0+ and LO_0- have
LO_0-	34		an internal 50 Ω connected to V _{CC} .
LI_1+	30	I	Inverting and non-inverting differential inputs of port_1 at the line side. LI_1+ and LI_1- have an
LI_1-	31		internal 50 Ω connected to an internal reference voltage. See <i>Figure 6</i> .
LO_1+	9	0	Inverting and non-inverting differential outputs of port_1 at the line side. LO_1+ and LO_1- have
 LO_1-	10		an internal 50 Ω connected to V _{CC} .
SWITCH SID	E HIGH SPEE	D DIFI	FERENTIAL IO's
SOA_0+	46	0	Inverting and non-inverting differential outputs of mux_0 at the switch_A side. SOA_0+ and SOA_0
SOA_0-	45	Ŭ	- have an internal 50 Ω connected to V _{CC} .
SOB_0+	4	0	Inverting and non-inverting differential outputs of mux_0 at the switch_B side. SOB_0+ and SOB_0
SOB_0+	3	0	
			- have an internal 50Ω connected to V_{CC} .
SIA_0+	40 39	I	Inverting and non-inverting differential inputs to the mux_0 at the switch_A side. SIA_0+ and SIA_0
SIA_0-			- have an internal 50 Ω connected to an internal reference voltage. See <i>Figure 6</i> .
SIB_0+	43	I	Inverting and non-inverting differential inputs to the mux_0 at the switch_B side. SIB_0+ and SIB_0
SIB_0-	42		- have an internal 50 Ω connected to an internal reference voltage. See <i>Figure 6</i> .
SOA_1+	22	0	Inverting and non-inverting differential outputs of mux_1 at the switch_A side. SOA_1+ and SOA_1
SOA_1-	21		– have an internal 50 Ω connected to V _{CC} .
SOB_1+	28	0	Inverting and non-inverting differential outputs of mux_1 at the switch_B side. SOB_1+ and SOB_1
SOB_1-	27		– have an internal 50 Ω connected to V _{CC} .
SIA_1+	16	I	Inverting and non-inverting differential inputs to the mux_1 at the switch_A side. SIA_1+ and SIA_1
SIA_1-	15		– have an internal 50 Ω connected to an internal reference voltage. See <i>Figure 6</i> .
SIB_1+	19	I	Inverting and non-inverting differential inputs to the mux_1 at the switch_B side. SIB_1+ and SIB_1
SIB_1-	18		– have an internal 50 Ω connected to an internal reference voltage. See <i>Figure 6</i> .
CONTROL (3	3.3V LVCMOS)	
MUX_S0	37	I	A logic low at MUX_S0 selects mux_0 to switch B. MUX_S0 is internally pulled high. Default state
_			for mux_0 is switch A.
MUX_S1	13	I	A logic low at MUX_S1 selects mux_1 to switch B. MUX_S0 is internally pulled high. Default state
			for mux_1 is switch A.
PREL_0	12	I	PREL_0 and PREL_1 select the output pre-emphasis of the line side drivers (LO_0± and LO_1±).
PREL_1	1		PREL_0 and PREL_1 are internally pulled high. See <i>Table 3</i> for line side pre-emphasis levels.
PRES_0	36	I	PRES_0 and PRES_1 select the output pre-emphasis of the switch side drivers (SOA_0±, SOB_0
PRES_1	25		±, SOA_1± and SOB_1±). PRES_0 and PRES_1 are internally pulled high. See Table 4 for switch
			side pre-emphasis levels.
LB0A	47	I	A logic low at LB0A enables the internal loopback path from SIA_0± to SOA_0±. LB0A is internally
			pulled high.
LB0B	48	I	A logic low at LB0B enables the internal loopback path from SIB_0± to SOB_0±. LB0B is internally
			pulled high.
LB1A	23	1	A logic low at LB1A enables the internal loopback path from SIA_1± to SOA_1±. LB1A is internally
			pulled high.
LB1B	24	1	A logic low at LB1B enables the internal loopback path from SIB_1± to SOB_1±. LB1B is internally
			pulled high.
RSV	26	1	Reserve pin to support factory testing. This pin can be left open, or tied to GND, or tied to GND

٦

Pin Name	Pin Number	I/O	Description
POWER	•		
V _{CC}	2, 8, 14, 20,	Р	$V_{CC} = 3.3V \pm 5\%.$
	29, 35, 38, 44		Each V_{CC} pin should be connected to the V_{CC} plane through a low inductance path, typically with a via located as close as possible to the landing pad of the V_{CC} pin.
			It is recommended to have a 0.01 μF or 0.1 $\mu F,$ X7R, size-0402 bypass capacitor from each V_{CC} pin to ground plane.
GND	5, 11, 17, 32, 41	Ρ	Ground reference. Each ground pin should be connected to the ground plane through a low inductance path, typically with a via located as close as possible to the landing pad of the GND pin.
GND	DAP	Ρ	Die Attach Pad (DAP) is the metal contact at the bottom side, located at the center of the LLP-48 package. It should be connected to the GND plane with at least 4 via to lower the ground impedance and improve the thermal performance of the package.

Note: I = Input, O = Output, P = Power

Note: All CML Inputs or Outputs must be AC coupled.

Functional Description

The DS25MB200 is a signal conditioning 2:1 multiplexer and a 1:2 buffer designed to support port redundancy up to 2.5 Gbps. The high speed inputs are self-biased to about 1.3V and are designed for AC coupling, see Figure 6 for details. The inputs are compatible to most AC coupling differential signals such as LVDS, LVPECL and CML. The DS25MB200 is not designed to operate with data rates below 250 Mbps or with a DC bias applied to the CML inputs or outputs. Most high speed links are encoded for DC balance and have been defined to include AC coupling capacitors allowing the DS25MB200 to be directly inserted into the datapath without any limitation. The ideal AC coupling capacitor value is often based on the lowest frequency component embedded within the serial link. A typical AC coupling capacitor value ranges between 100 and 1000nF, some specifications with scrambled data may require a larger capacitor for optimal performance. To reduce unwanted parasitics around and within the AC coupling capacitor, a body size of 0402 is recommended. *Figure 5* shows the AC coupling capacitor placement in an AC test circuit.

Each input stage has a fixed equalizer that provides equalization to compensate about 5 dB of transmission loss from a short backplane trace (about 10 inches backplane). The output driver has Pre-emphasis (driver-side equalization) to compensate the transmission loss of the backplane that it is driving. The driver conditions the output signal such that the lower frequency and higher frequency pulses reach approximately the same amplitude at the end of the backplane, and minimize the deterministic jitter caused by the amplitude disparity. The DS25MB200 provides four steps of user-selectable Pre-emphasis ranging from 0, -3, -6 and -9 dB to handle different lengths of backplane. Figure 1 shows a driver Pre-emphasis waveform. The Pre-emphasis duration is 188ps nominal, corresponds to 0.47 bit-width at 2.5 Gbps. The Pre-emphasis levels of switch-side and line-side can be individually programmed.

TABLE 1. LOGIC TABLE FOR MULTIPLEX CONTROLS

MUX_S0	Mux Function
0	MUX_0 select switch_B input, SIB_0±.
1 (default)	MUX_0 select switch_A input, SIA_0±.
MUX_S1	Mux Function
0	MUX_1 select switch_B input, SIB_1±.
1 (default)	MUX_1 select switch_A input, SIA_0±.

TABLE 2. LOGIC TABLE FOR LOOPBACK CONTROLS

LB0A	Loopback Function
0	Enable loopback from SIA_0± to SOA_0±.
1 (default)	Normal mode. Loopback disabled.
LB0B	Loopback Function
0	Enable loopback from SIB_0± to SOB_0±.
1 (default)	Normal mode. Loopback disabled.
LB1A	Loopback Function
0	Enable loopback from SIA_1± to SOA_1±.
1 (default)	Normal mode. Loopback disabled.
LB1B	Loopback Function
0	Enable loopback from SIB_1± to SOB_1±.
1 (default)	Normal mode. Loopback disabled.

TABLE 3. LINE-SIDE PRE-EMPHASIS CONTROLS

PreL_[1:0]	Pre-Emphasis Level in mV _{PP} (VODB)	De-Emphasis Level in mV _{PP} (VODPE)	Pre-Emphasis in dB (VODPE/VODB)	Typical FR4 board trace
0 0	1200	1200	0	10 inches
0 1	1200	849.53	-3	20 inches
10	1200	600	-6	30 inches
1 1 (default)	1200	425.78	-9	40 inches

TABLE 4. SWITCH-SIDE PRE-EMPHASIS CONTROLS

PreS_[1:0]	Pre-Emphasis Level in mV _{pp} (VODB)	De-Emphasis Level in mV _{PP} (VODPE)	Pre-Emphasis in dB (VODPE/VODB)	Typical FR4 board trace
0 0	1200	1200	0	10 inches
0 1	1200	849.53	-3	20 inches
10	1200	600	-6	30 inches
1 1 (default)	1200	425.78	-9	40 inches

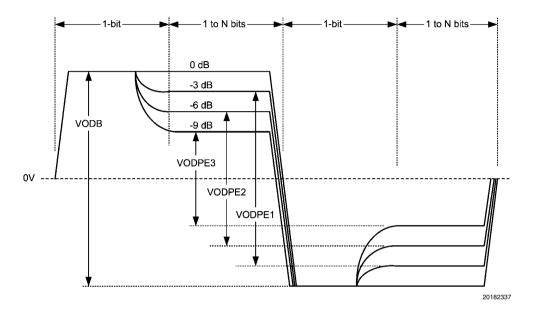


FIGURE 1. Driver Pre-Emphasis Differential Waveform (showing all 4 pre-emphasis steps)

DS25MB200

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

–0.3V to 4V
–0.3V to
(V _{CC} +0.3V)
–0.3V to
(V _{CC} +0.3V)
+150°C
-65°C to +150°C
+260°C
33.7°C/W

Thermal Resistance, θ_{JC-top}	20.7°C/W
Thermal Resistance, $\theta_{JC-bottom}$	5.8°C/W
Thermal Resistance, Φ_{JB}	18.2°C/W
ESD Rating HBM, 1.5 kΩ, 100 pF	6 kV

Recommended Operating Ratings

	Min	Тур	Мах	Units
Supply Voltage (V _{CC} -GND)	3.135	3.3	3.465	V
Supply Noise Amplitude 10 Hz to 2 GHz			50	mV_{PP}
Ambient Temperature	-40		85	°C
Case Temperature			100	°C

Electrical Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
LVCMOS D	C SPECIFICATIONS	•		•		
V _{IH}	High Level Input Voltage		2.0		V _{CC} +0.3	V
V _{IL}	Low Level Input Voltage		-0.3		0.8	V
I _{IH}	High Level Input Current	V _{IN} = V _{CC}	-10		10	μA
I	Low Level Input Current	V _{IN} = GND	75	94	124	μA
R _{PU}	Pull-High Resistance			35		kΩ
RECEIVER	SPECIFICATIONS	•				
V _{ID}	Differential Input Voltage Range	AC Coupled Differential Signal Below 1.25 Gbps Above 1.25 Gbps Measured at input pins.	100 100		1750 1560	mV _{P-P} mV _{P-P}
V _{ICM}	Common Mode Voltage at Receiver Inputs	Measured at receiver inputs reference to ground.		1.5		V
R _{ITD}	Input Differential Termination	On-chip differential termination between IN+ or IN 	84	100	116	Ω
DRIVER SP	ECIFICATIONS				- <u>-</u>	
VODB	Output Differential Voltage Swing without Pre-Emphasis	$R_L = 100\Omega \pm 1\%$ PRES_1=PRES_0=0 PREL_1=PREL_0=0 Driver pre-emphasis disabled. Running K28.7 pattern at 2.5 Gbps. See <i>Figure 5</i> for test circuit.	1000	1200	1400	mV _{P-P}

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
V _{PE}	Output Pre-Emphasis Voltage Ratio 20*log(VODPE/VODB)	$R_{L} = 100\Omega \pm 1\%$ Running K28.7 pattern at 2.5 Gbps $PREx_{[1:0]=00$ $PREx_{[1:0]=01$ $PREx_{[1:0]=10$ $PREx_{[1:0]=11}$ x=S for switch side pre-emphasis control x=L for line side pre-emphasis control See Figure 1 on waveform. See Figure 5 for test circuit.		0 -3 -6 -9		dB dB dB
t _{PE}	Pre-Emphasis Width	Tested at -9 dB pre-emphasis level, PREx[1:0]=11 x=S for switch side pre-emphasis control x=L for line side pre-emphasis control See <i>Figure 4</i> on measurement condition.	125	188	400	ps
R _{OTSE}	Output Termination	On-chip termination from OUT+ or OUT- to V _{CC}	42	50	58	Ω
R _{OTD}	Output Differential Termination	On-chip differential termination between OUT+ and OUT-		100		Ω
ΔR _{OTSE}	Mis-Match in Output Termination Resistors	Mis-match in output terminations at OUT+ and OUT-			5	%
V _{OCM}	Output Common Mode Voltage		2.4		2.9	V
POWER DI	SSIPATION	L				
P _D	Power Dissipation	$V_{DD} = 3.465V$ All outputs terminated by $100\Omega \pm 1\%$. PREL_[1:0]=0, PRES_[1:0]=0 Running PRBS 2 ⁷ -1 pattern at 2.5 Gbps			1	W
AC CHARA	CTERISTICS					
t _R	Differential Low to High Transition Time	Measured with a clock-like pattern at 100 MHz, between 20% and 80% of the differential output		80		ps
t _F	Differential High to Low Transition Time	voltage. Pre-emphasis disabled. Transition time is measured with fixture as shown in <i>Figure 5</i> , adjusted to reflect the transition time at the output pins.		80		ps
t _{PLH}	Differential Low to High Propagation Delay	Measured at 50% differential voltage from input to output.		0.5	2	ns
t _{PHL}	Differential High to Low Propagation Delay			0.5	2	ns
t _{SKP}	Pulse Skew	It _{PHL} -t _{PLH}			20	ps
t _{sko}	Output Skew (Note 7)	Difference in propagation delay between two outputs in the same device.			200	ps
t _{skpp}	Part-to-Part Skew	Difference in propagation delay between the same output from devices operating under identical conditions.			500	ps
t _{SM}	Mux Switch Time	Measured from V_{IH} or V_{IL} of the mux-control or loopback control to 50% of the valid differential output.		1.8	6	ns
RJ	Device Random Jitter (Note 5)	See <i>Figure 5</i> for test circuit. Alternating-1-0 pattern. Pre-emphasis disabled. At 1.25 Gbps At 2.5 Gbps			2 2	psrms psrms

DS25MB200

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
DJ	Device Deterministic Jitter (Note 6)	See <i>Figure 5</i> for test circuit. Pre-emphasis disabled. Between 0.8 and 2.5 Gbps with PRBS7 pattern for DS25MB200 @ -40°C to 85°C			30	Pspp
DR _{MAX}	Maximum Data Rate	Tested with alternating 1-0 pattern	2.5			Gbps
DR _{MIN}	Minimum Data Rate	(Note 8)			0.6	Gbps

Note 1: "Absolute Maximum Ratings" are the ratings beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits.

Note 2: Typical parameters measured at V_{CC} = 3.3V, T_A = 25°C. They are for reference purposes and are not production-tested.

Note 3: IN+ and IN- are generic names refer to one of the many pairs of complimentary inputs of the DS25MB200. OUT+ and OUT- are generic names refer to one of the many pairs of the complimentary outputs of the DS25MB200. Differential input voltage V_{ID} is defined as IN+-IN-I. Differential output voltage V_{OD} is defined as IOUT+-OUT-I.

Note 4: K28.7 pattern is a 10-bit repeating pattern of K28.7 code group {001111 1000}

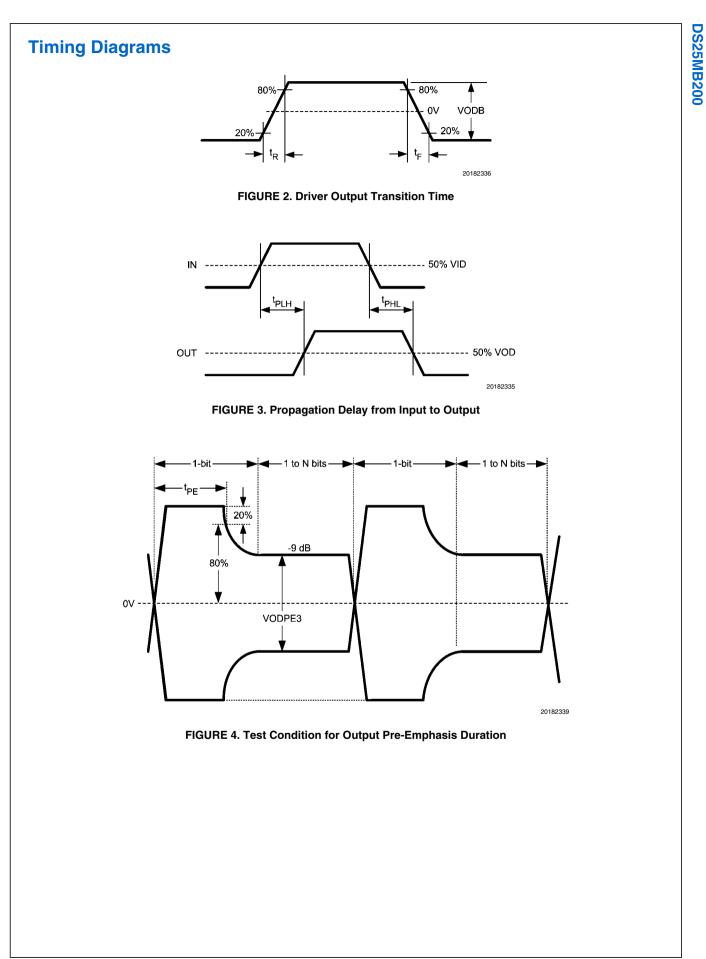
K28.5 pattern is a 20-bit repeating pattern of +K28.5 and -K28.5 code groups {110000 0101 001111 1010}

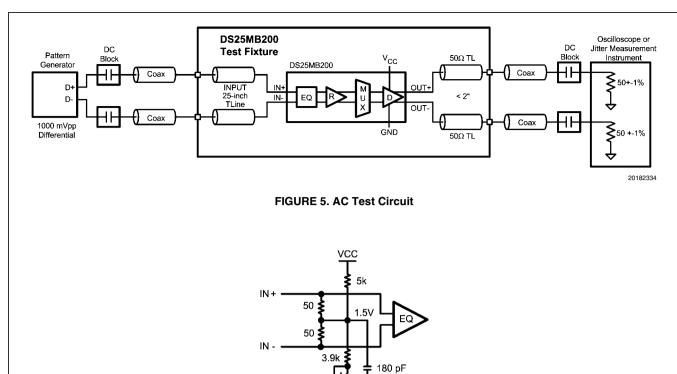
Note 5: Device output random jitter is a measurement of the random jitter contribution from the device. It is derived by the equation $sqrt(RJ_{OUT}^2 - RJ_{IN}^2)$, where RJ_{OUT} is the random jitter measured at the output of the device in psrms, RJ_{IN} is the random jitter of the pattern generator driving the device.

Note 6: Device output deterministic jitter is a measurement of the deterministic jitter contribution from the device. It is derived by the equation (DJ_{OUT}-DJ_{IN}), where DJ_{OUT} is the peak-to-peak deterministic jitter measured at the output of the device in pspp, DJ_{IN} is the peak-to-peak deterministic jitter of the pattern generator driving the device.

Note 7: t_{SKO} is the magnitude difference in the propagation delays among data paths between switch A and switch B of the same port and similar data paths between port 0 and port 1. An example is the output skew among data paths from SIA_0± to LO_0±, SIB_0± to LO_0±, SIA_1± to LO_1± and SIB_1± to LO_1±. Another example is the output skew among data paths from LI_0± to SOA_0±, LI_0± to SOB_0±, LI_1± to SOA_1± and LI_1± to SOB_1±. t_{SKO} also refers to the delay skew of the loopback paths of the same port and between similar data paths between port 0 and port 1. An example is the output skew among data paths from SIA_0± to SOB_0±, LI_0± to SOA_0±, SIB_0± to SOA_1± and LI_1± to SOB_1±. t_{SKO} also refers to the delay skew of the loopback paths of the same port and between similar data paths between port 0 and port 1. An example is the output skew among data paths SIA_0± to SOA_0±, SIB_0± to SOB_0±, SIA_1± to SOA_1± and SIB_1± to SOB_1±.

Note 8: For operation under 1 Gbps, encoded data transmission is recommended (i.e. 8b10b).





20182350

FIGURE 6. Receiver Input Termination and Biasing Circuit

Application Information

The DS25MB200 input equalizer provides equalization to compensate about 5 dB of transmission loss from a short backplane transmission line. For characterization purposes, a 25-inch FR4 coupled micro-strip board trace is used in place

of the short backplane link. The 25-inch microstrip board trace has approximately 5 dB of attenuation between 375 MHz and 1.875 GHz, representing closely the transmission loss of the short backplane transmission line. The 25-inch microstrip is connected between the pattern generator and the differential inputs of the DS25MB200 for AC measurements.

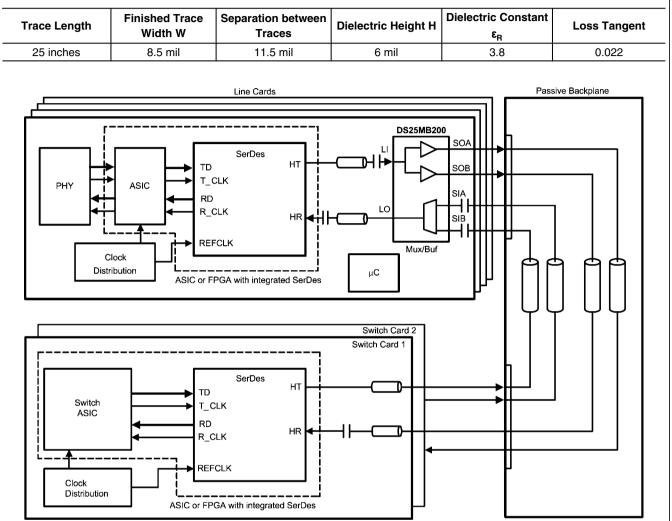
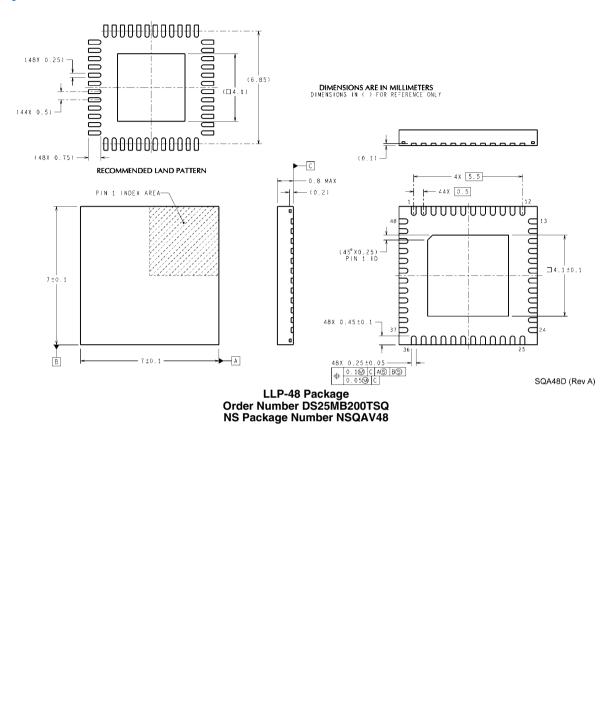


FIGURE 7. Application Diagram (showing data paths of port 0)

DS25MB200

20182344

Physical Dimensions inches (millimeters) unless otherwise noted



Notes

Notes

For more National Semiconductor product information and proven design tools, visit the following Web sites at:

Products		Design Support	
Amplifiers	www.national.com/amplifiers	WEBENCH® Tools	www.national.com/webench
Audio	www.national.com/audio	App Notes	www.national.com/appnotes
Clock and Timing	www.national.com/timing	Reference Designs	www.national.com/refdesigns
Data Converters	www.national.com/adc	Samples	www.national.com/samples
Interface	www.national.com/interface	Eval Boards	www.national.com/evalboards
LVDS	www.national.com/lvds	Packaging	www.national.com/packaging
Power Management	www.national.com/power	Green Compliance	www.national.com/quality/green
Switching Regulators	www.national.com/switchers	Distributors	www.national.com/contacts
LDOs	www.national.com/ldo	Quality and Reliability	www.national.com/quality
LED Lighting	www.national.com/led	Feedback/Support	www.national.com/feedback
Voltage Reference	www.national.com/vref	Design Made Easy	www.national.com/easy
PowerWise® Solutions	www.national.com/powerwise	Solutions	www.national.com/solutions
Serial Digital Interface (SDI)	www.national.com/sdi	Mil/Aero	www.national.com/milaero
Temperature Sensors	www.national.com/tempsensors	SolarMagic™	www.national.com/solarmagic
Wireless (PLL/VCO)	www.national.com/wireless	Analog University®	www.national.com/AU

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS.

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS, NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2009 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Technical Support Center Email: support@nsc.com Tel: 1-800-272-9959

National Semiconductor Europe Technical Support Center Email: europe.support@nsc.com National Semiconductor Asia Pacific Technical Support Center Email: ap.support@nsc.com National Semiconductor Japan Technical Support Center Email: jpn.feedback@nsc.com